
DISCRETE POWER DIODES and THYRISTORS
DATA BOOK

FAST RECOVERY DIODES

Stud Version

Features

- High power FAST recovery diode series
- 2.0 to 3.0 μ s recovery time
- High voltage ratings up to 2500V
- High current capability
- Optimized turn on and turn off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Compression bonded encapsulation
- Stud version case style B-8
- Maximum junction temperature 150°C

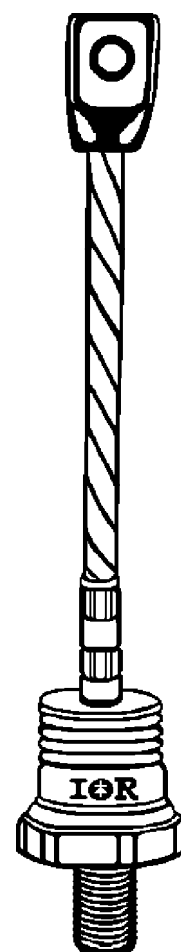
400A
450A

Typical Applications

- Snubber diode for GTO
- High voltage free-wheeling diode
- Fast recovery rectifier applications

Major Ratings and Characteristics

Parameters	SD453N/R		Units
	S20	S30	
$I_{F(AV)}$	400	450	A
@ T_C	70	70	°C
$I_{F(RMS)}$	630	710	A
I_{FSM} @ 50Hz	9300	9600	A
@ 60Hz	9730	10050	A
V_{RRM} range	1200 to 2500	1200 to 2500	V
t_{rr}	2.0	3.0	μ s
@ T_J	25	25	°C
T_J	- 40 to 150		°C



case style
B-8

ELECTRICAL SPECIFICATIONS

Voltage Ratings

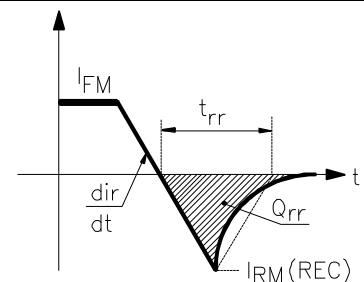
Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak rev. voltage V	I_{RRM} max. @ $T_J = T_J$ max. mA
SD453N/R	12	1200	1300	50
	16	1600	1700	
	20	2000	2100	
	25	2500	2600	

Forward Conduction

Parameter		SD453N/R		Units	Conditions			
		S20	S30					
I _{F(AV)}	Max. average forward current @ case temperature	400	450	A	180° conduction, half sine wave			
		70	70	°C				
I _{F(RMS)}	Max. RMS forward current @ case temperature	630	710	A				
		55	52	°C				
I _{FSM}	Max. peak, one-cycle forward, non-repetitive surge current	9300	9600	A	t = 10ms	No voltage	Sinusoidal half wave, Initial T _J = T _J max.	
		9730	10050		t = 8.3ms	reapplied		
		7820	8070		t = 10ms	100% V _{RRM}		
		8190	8450		t = 8.3ms	reapplied		
I ² t	Maximum I ² t for fusing	432	460	KA ² s	t = 10ms	No voltage		
		395	420		t = 8.3ms	reapplied		
		306	326		t = 10ms	100% V _{RRM}		
		279	297		t = 8.3ms	reapplied		
I ² √t	Maximum I ² √t for fusing	4320	4600	KA ² √s	t = 0.1 to 10ms, no voltage reapplied			
V _{F(TO)1}	Low level value of threshold voltage	1.00	0.95	V	(16.7% x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J max.			
V _{F(TO)2}	High level value of threshold voltage	1.09	1.04		(I > π x I _{F(AV)}), T _J = T _J max.			
r _{f1}	Low level value of forward slope resistance	0.80	0.60	mΩ	(16.7% x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J max.			
r _{f2}	High level value of forward slope resistance	0.74	0.54		(I > π x I _{F(AV)}), T _J = T _J max.			
V _{FM}	Max. forward voltage drop	2.20	1.85	V	I _{pk} = 1500A, T _J = T _J max, t _p = 10ms sinusoidal wave			

Recovery Characteristics

Code	$T_J = 25^\circ\text{C}$ typical t_{rr} @ 25% I_{RRM} (μs)	Test conditions			Max. values @ $T_J = 150^\circ\text{C}$		
		I_{pk} Square Pulse (A)	di/dt (A/μs)	V_r (V)	t_{rr} @ 25% I_{RRM} (μs)	Q_{rr} (μC)	I_{rr} (A)
S20	2.0	1000	50	-50	3.5	250	120
S30	3.0	1000	50	-50	5.0	380	150



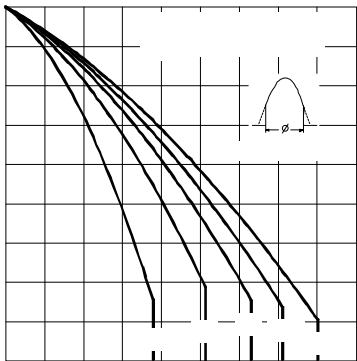


Fig. 1 - Current Ratings Characteristics

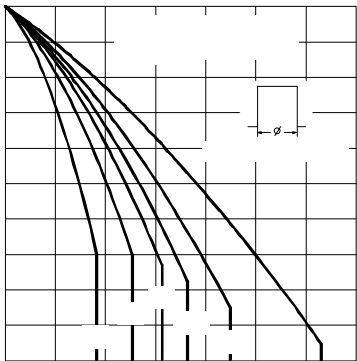


Fig. 2 - Current Ratings Characteristics

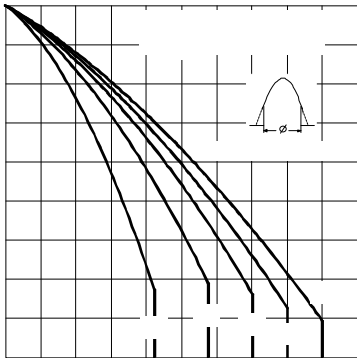


Fig. 3 - Current Ratings Characteristics

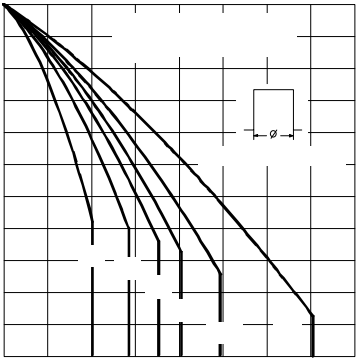


Fig. 4 - Current Ratings Characteristics

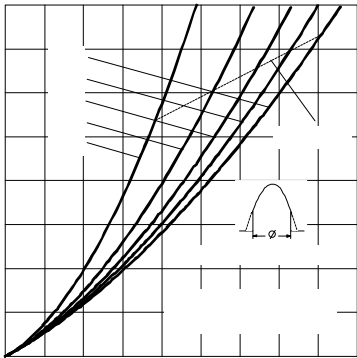


Fig. 5 - Forward Power Loss Characteristics

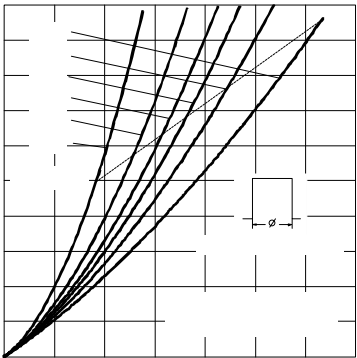


Fig. 6 - Forward Power Loss Characteristics

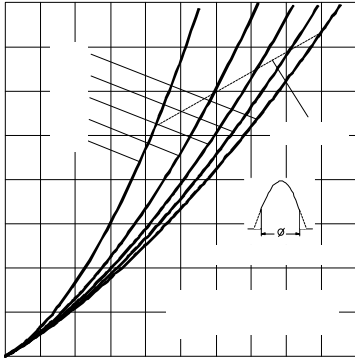


Fig. 7 - Forward Power Loss Characteristics

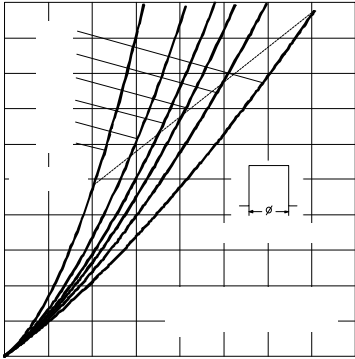


Fig. 8 - Forward Power Loss Characteristics

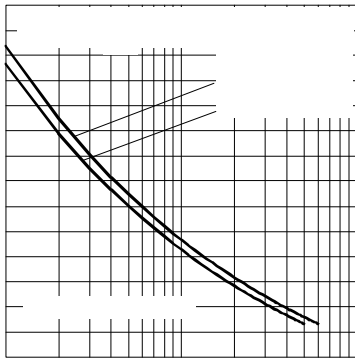


Fig. 9 - Maximum Non-repetitive Surge Current

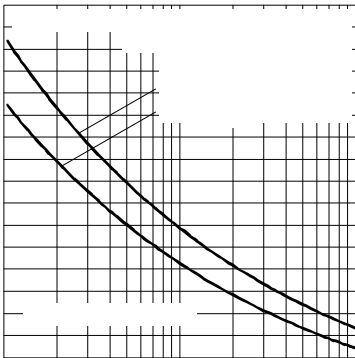


Fig. 10 - Maximum Non-repetitive Surge Current

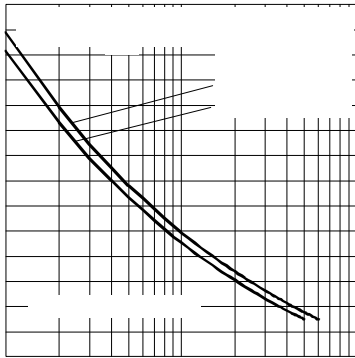


Fig.11 - Maximum Non-repetitive Surge Current

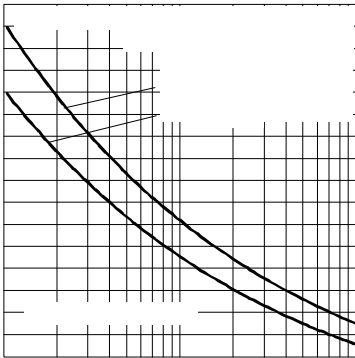


Fig.12 - Maximum Non-repetitive Surge Current

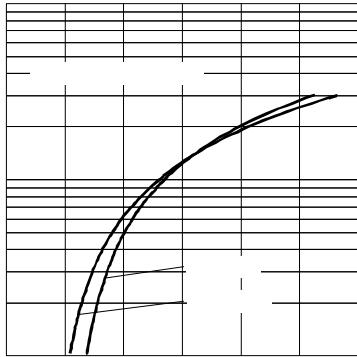


Fig. 13 - Forward Voltage Drop Characteristics

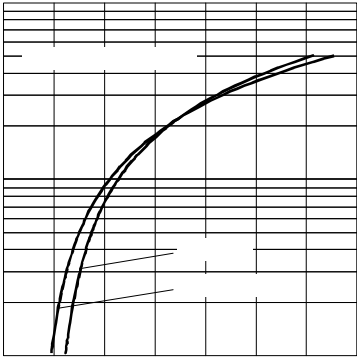


Fig. 14 - Forward Voltage Drop Characteristics

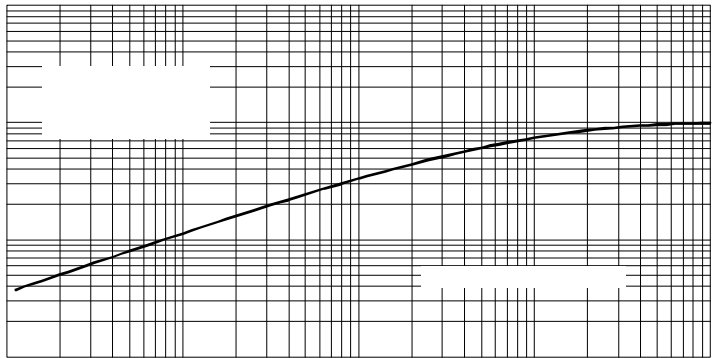


Fig. 15 - Thermal Impedance Z_{thJC} Characteristic

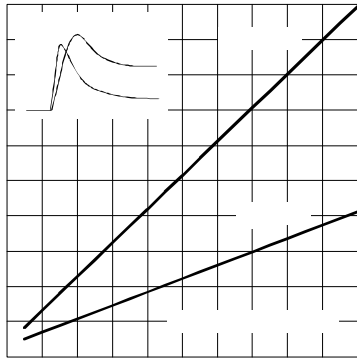


Fig. 16 - Typical Forward Recovery Characteristics

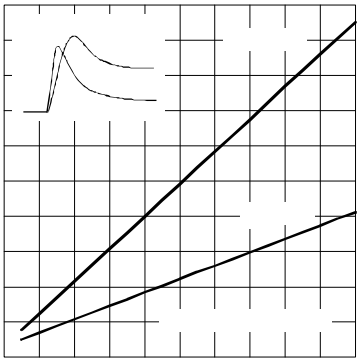


Fig. 17 - Typical Forward Recovery Characteristics

SD453N/R Series

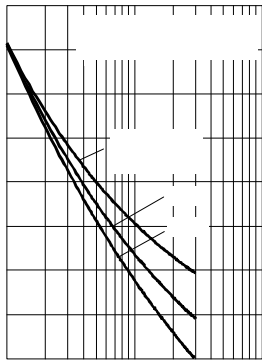


Fig. 18 - Recovery Time Characteristics

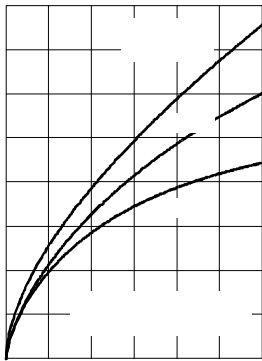


Fig. 19 - Recovery Charge Characteristics

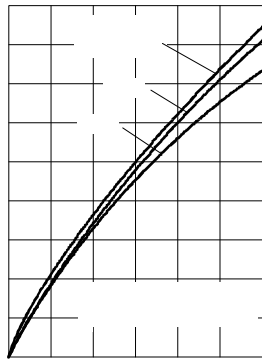


Fig. 20 - Recovery Current Characteristics

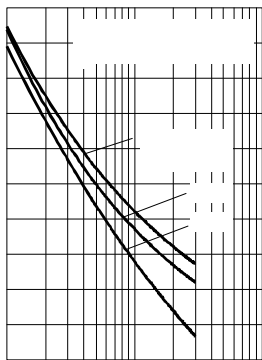


Fig. 21 - Recovery Time Characteristics

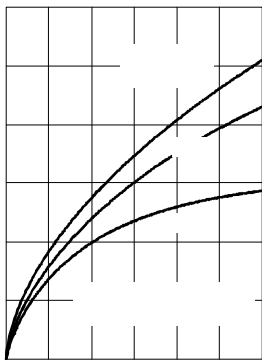


Fig. 22 - Recovery Charge Characteristics

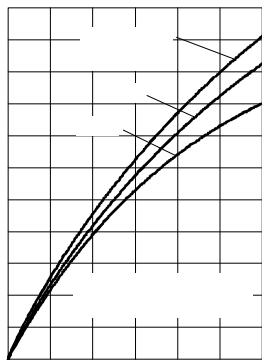


Fig. 23 - Recovery Current Characteristics

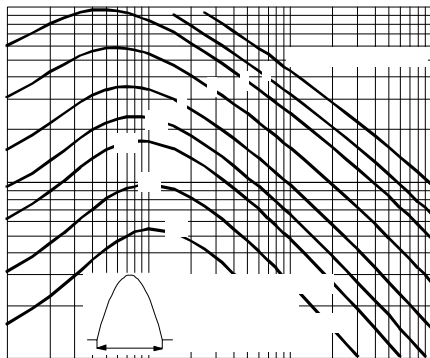


Fig. 24 - Maximum Total Energy Loss Per Pulse Characteristics

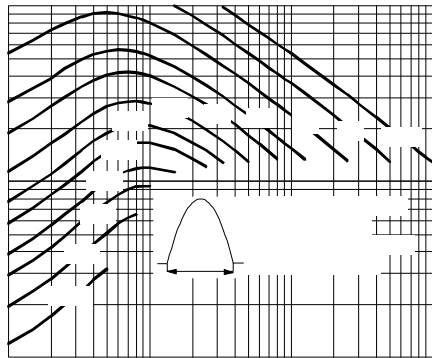


Fig. 25 - Frequency Characteristics

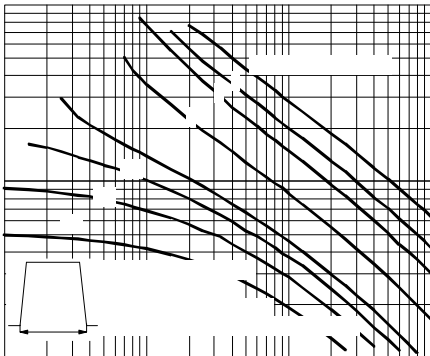


Fig. 26 - Maximum Total Energy Loss Per Pulse Characteristics

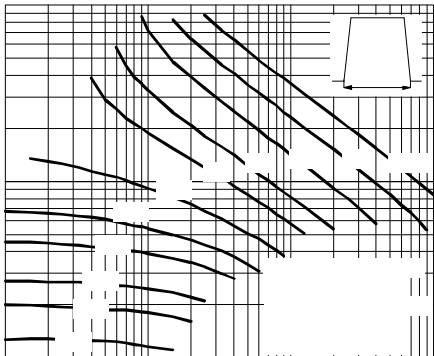


Fig. 27 - Frequency Characteristics

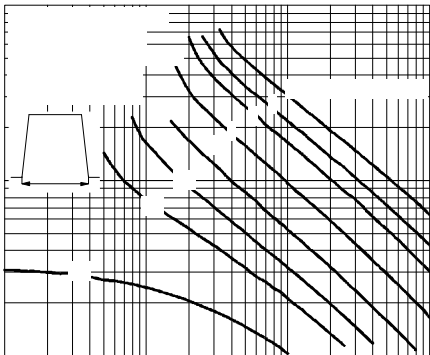


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

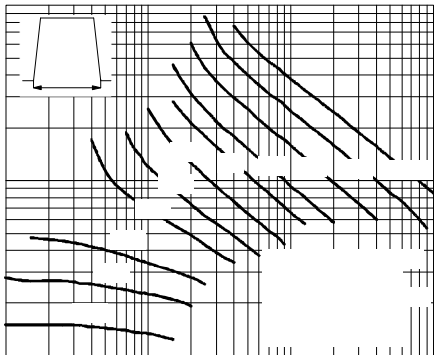


Fig. 29 - Frequency Characteristics

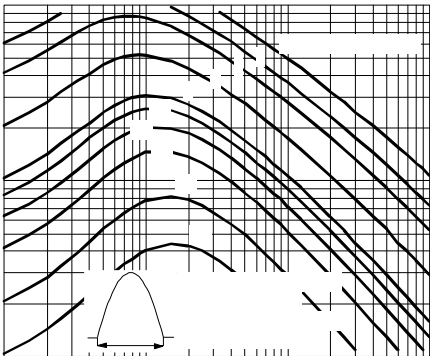


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

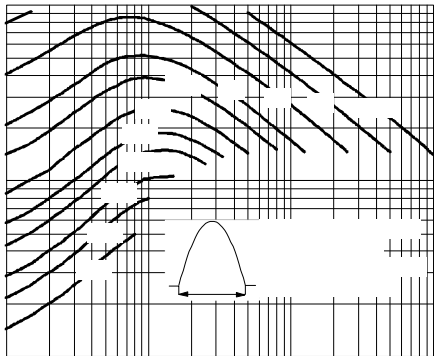


Fig. 31 - Frequency Characteristics

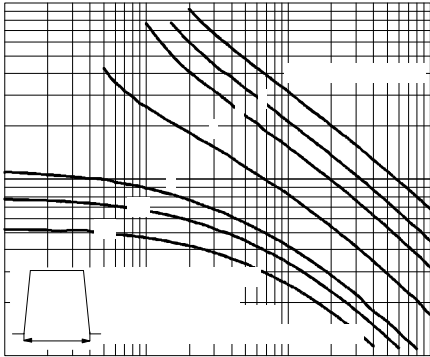


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

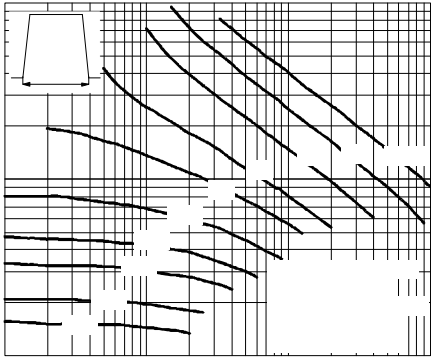


Fig. 33 - Frequency Characteristics

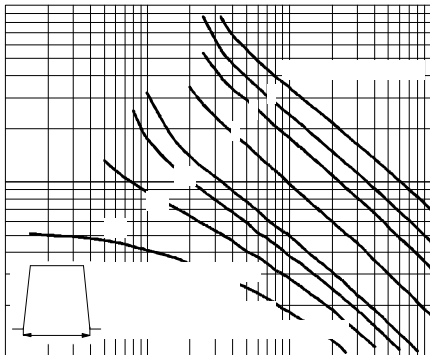


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

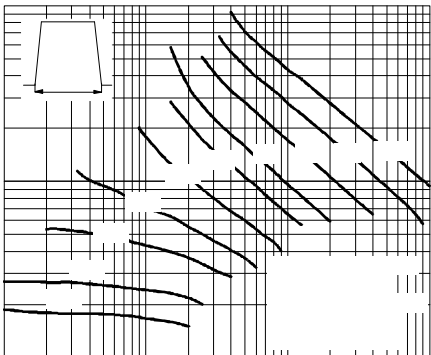


Fig. 35 - Frequency Characteristics

Thermal and Mechanical Specifications

Parameter		SD453N/R		Units	Conditions
		S20	S30		
T _j	Max. junction operating temperature range	-40 to 150		°C	
T _{stg}	Max. storage temperature range	-40 to 150			
R _{thJC}	Max. thermal resistance, junction to case	0.1		K/W	DC operation
R _{thCS}	Max. thermal resistance, case to heatsink	0.04			Mounting surface, smooth, flat and greased
T	Mounting torque, ± 10%	50		Nm	Not lubricated threads
wt	Approximate weight	454		g	
Case style		B - 8			See Outline Table

 ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	S20	S30	S20	S30		
180°	0.010	0.010	0.008	0.008	K/W	$T_j = T_j \text{ max.}$
120°	0.014	0.014	0.014	0.014		
90°	0.017	0.017	0.019	0.019		
60°	0.025	0.025	0.026	0.026		
30°	0.042	0.042	0.042	0.042		

Ordering Information Table

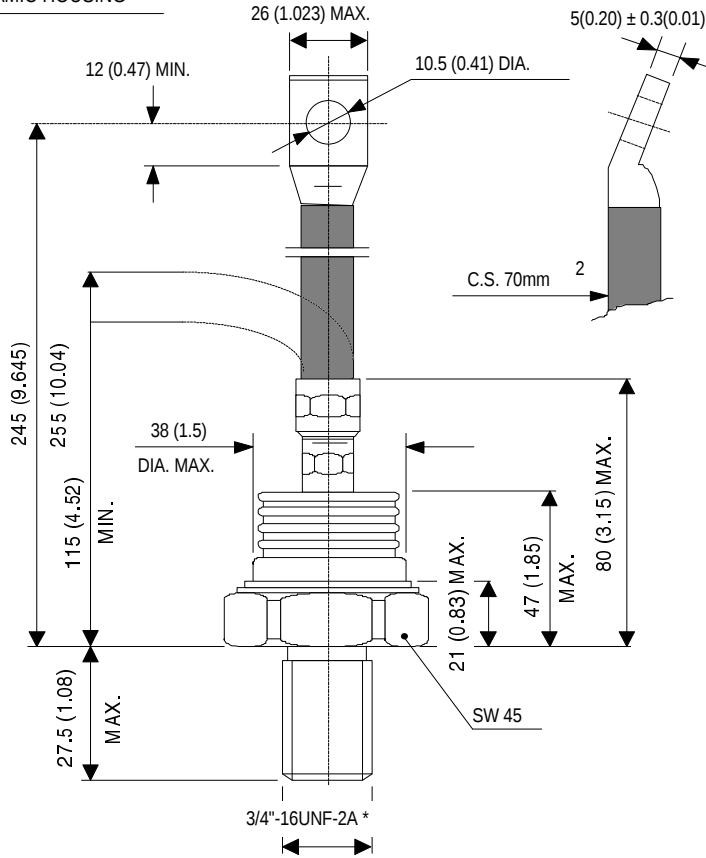
Device Code

SD	45	3	N	25	S30	P	S	C
①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Diode
- 2** - Essential part number
- 3** - 3 = Fast recovery
- 4** - N = Stud Normal Polarity (Cathode to Stud)
R = Stud Reverse Polarity (Anode to Stud)
- 5** - Voltage code: Code $\times 100 = V_{RRM}$ (see Voltage Ratings table)
- 6** - t_{rr} code (see Recovery Characteristics table)
- 7** - P = Stud base B-8 3/4" 16UNF-2A
M = Stud base B-8 M24 X 1.5
- 8** - S = Isolated lead with silicone sleeve
(Red = Reverse Polarity; Blue = Normal Polarity)
None = Not isolated lead
T = Threaded Top Terminal 3/8" 24UNF-2A
- 9** - C = Ceramic housing

Outlines Table

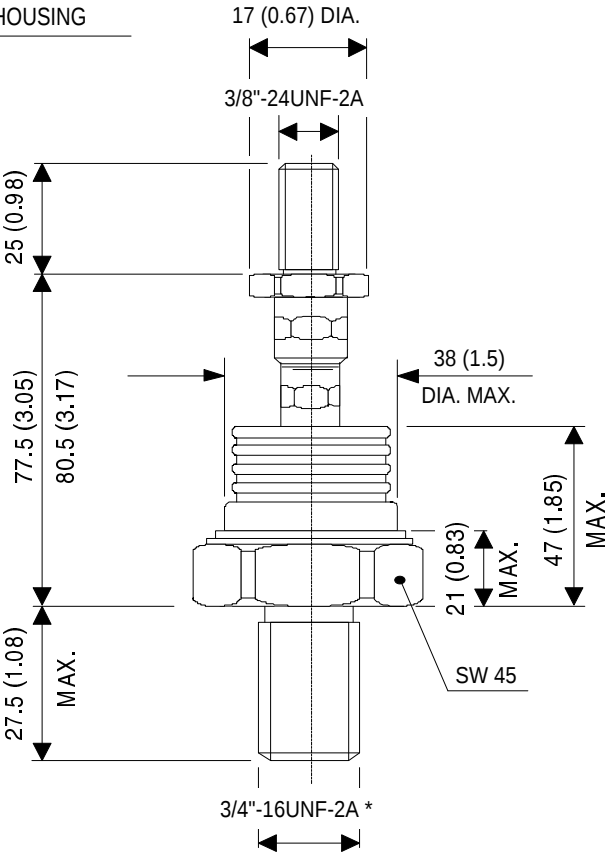
CERAMIC HOUSING



Case Style B-8
All dimensions in millimeters (inches)

* FOR METRIC DEVICE: M24 x 1.5 - SCREW LENGTH — 21(0.83) MAX.

CERAMIC HOUSING



Case Style B-8 with top thread terminal 3/8"
All dimensions in millimeters (inches)

* FOR METRIC DEVICE: M24 x 1.5 - SCREW LENGTH — 21(0.83) MAX.

Copyright © Each Manufacturing Company.

All Datasheets cannot be modified without permission.

This datasheet has been download from :

www.AllDataSheet.com

100% Free DataSheet Search Site.

Free Download.

No Register.

Fast Search System.

www.AllDataSheet.com